



安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

A1271

TO-92 Bipolar Transistor 双极型三极管

■ Features 特点

PNP General Purpose 通用

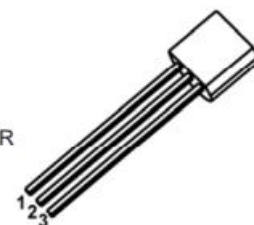
■ Absolute Maximum Ratings 最大额定值

TO - 92

1.EMITTER

2.COLLECTOR

3.BASE



Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Collector-Base Voltage 集电极基极电压	V_{CBO}	-35	V
Collector-Emitter Voltage 集电极发射极电压	V_{CEO}	-30	V
Emitter-Base Voltage 发射极基极电压	V_{EBO}	-5	V
Collector Current 集电极电流	I_C	-800	mA
Power dissipation 耗散功率	$P_C(T_a=25^\circ C)$	625	mW
Thermal Resistance Junction-Ambient 热阻	$R_{\theta JA}$	200	$^\circ C/W$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	-55to+150 $^\circ C$	

■ Device Marking 产品打标

$H_{FE}(1)$	100-200(O)	160-320(Y)
Mark	A1271	



■ Electrical Characteristics 电特性

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Type 典型值	Max 最大值	Unit 单位
Collector-Base Breakdown Voltage 集电极基极击穿电压($I_C = -100\mu\text{A}$, $I_E = 0$)	BV_{CBO}	-35	—	—	V
Collector-Emitter Breakdown Voltage 集电极发射极击穿电压($I_C = -10\text{mA}$, $I_B = 0$)	BV_{CEO}	-30	—	—	V
Emitter-Base Breakdown Voltage 发射极基极击穿电压($I_E = -100\mu\text{A}$, $I_C = 0$)	BV_{EBO}	-5	—	—	V
Collector-Base Leakage Current 集电极基极漏电流($V_{CB} = -35\text{V}$, $I_E = 0$)	I_{CBO}	—	—	-0.1	μA
Collector-Emitter Leakage Current 集电极发射漏电流($V_{CE} = -25\text{V}$, $I_E = 0$)	I_{CBO}	—	—	-0.2	μA
Emitter-Base Leakage Current 发射极基极漏电流($V_{EB} = -5\text{V}$, $I_C = 0$)	I_{EBO}	—	—	-0.1	μA
DC Current Gain 直流电流增益($V_{CE} = -1\text{V}$, $I_C = -100\text{mA}$)	$H_{FE(1)}$	100	—	320	
DC Current Gain 直流电流增益($V_{CE} = -1\text{V}$, $I_C = -700\text{mA}$)	$H_{FE(2)}$	35	—	—	
Collector-Emitter Saturation Voltage 集电极发射极饱和压降($I_C = -500\text{mA}$, $I_B = -20\text{mA}$)	$V_{CE(sat)}$	—	—	-0.7	V
Base-Emitter On Voltage 基极发射极导通电压($V_{CE} = -1\text{V}$, $I_C = -10\text{mA}$)	$V_{BE(on)}$	—	—	-0.8	V
Output Capacitance 输出电容($V_{CB} = -10\text{V}$, $I_E = 0$, $f = 1\text{MHz}$)	C_{ob}	—	19	—	pF
Transition Frequency 特征频率($V_{CE} = -5\text{V}$, $I_C = -10\text{mA}$)	f_T	—	120	—	MHz

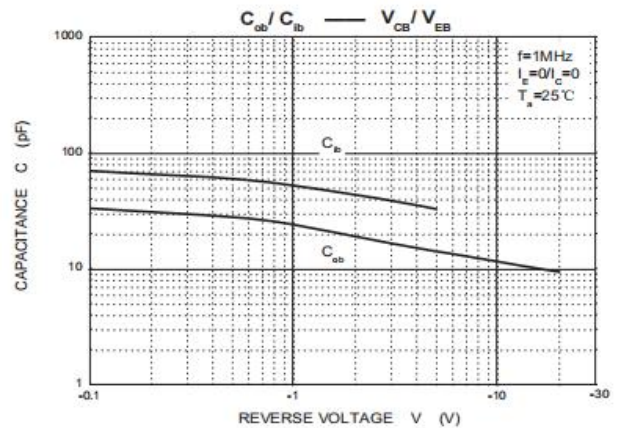
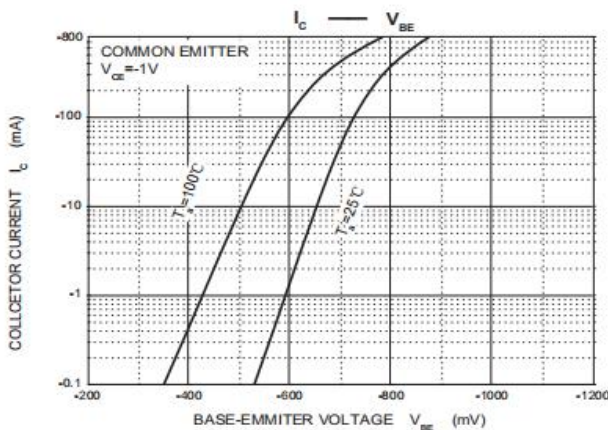
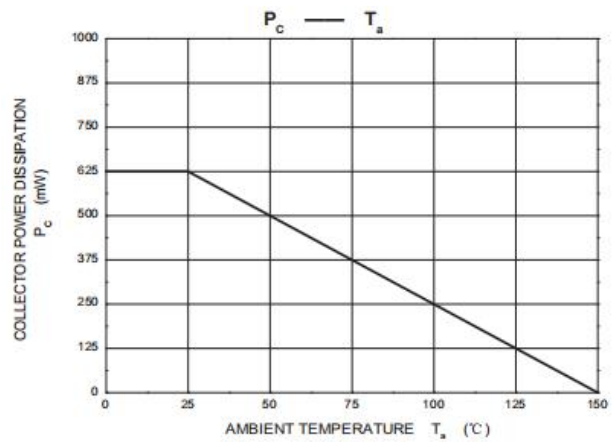
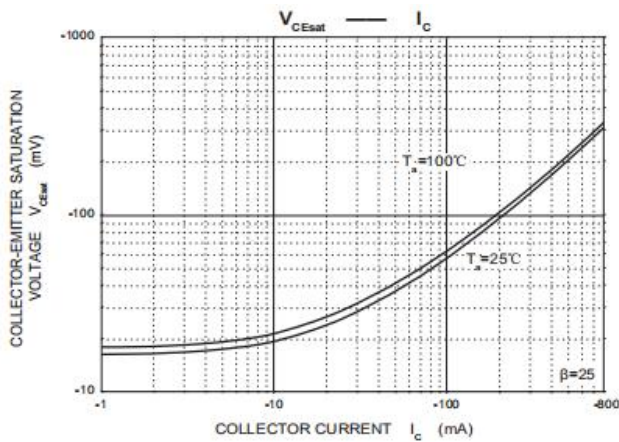
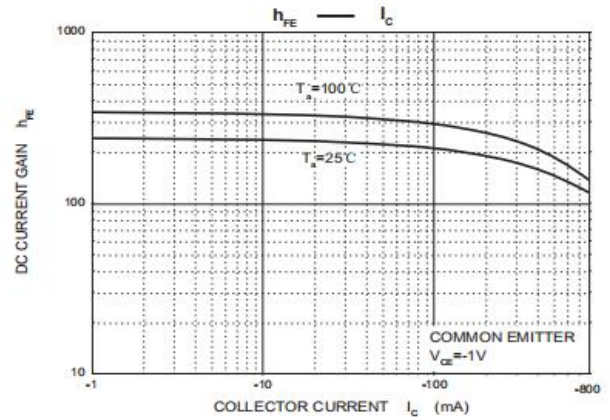
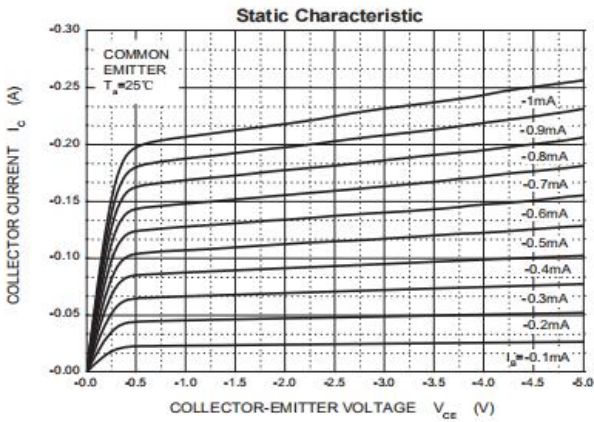


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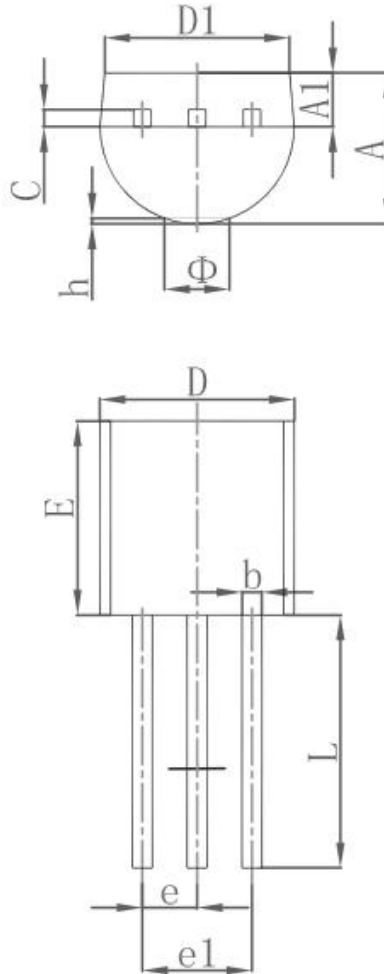
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Typical Characteristic Curve 典型特性曲线



■Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.300	4.700	0.169	0.185
D1	3.430		0.135	
E	4.300	4.700	0.169	0.185
e	1.270 TYP		0.050 TYP	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571
Φ		1.600		0.063
h	0.000	0.380	0.000	0.015